# SQ4401EY

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**Vishay Siliconix** 

# Automotive P-Channel 40 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY				
V <sub>DS</sub> (V)	- 40			
$R_{DS(on)}(\Omega)$ at $V_{GS}$ = - 10 V	0.014			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -4.5 V$	0.023			
I <sub>D</sub> (A)	- 17.3			
Configuration	Single			

#### FEATURES

- TrenchFET<sup>®</sup> Power MOSFET
- AEC-Q101 qualified
- 100 %  $R_q$  and UIS tested
- Material categorization: for definitions of compliance please see <u>www.vishav.com/doc?99912</u>

G

S

P-Channel MOSFET



ROHS COMPLIANT HALOGEN FREE

·D ( • 9		
Configuration	Single	
ORDERING INFORMATION		
Package		SO-8
Lead (Pb)-free and halogen-free		SQ4401EY (for detailed order number please see <u>www.vishay.com/doc?79771</u> )

<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>C</sub> = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V <sub>DS</sub>	- 40		
Gate-source voltage		V <sub>GS</sub>	± 20	V	
Orational during annual a	T <sub>C</sub> = 25 °C		- 17.3		
Continuous drain current <sup>a</sup>	T <sub>C</sub> = 125 °C	ID ID	- 10		
Continuous source current (diode conduction) a		I <sub>S</sub>	- 6.5	А	
Pulsed drain current <sup>b</sup>		I <sub>DM</sub>	- 69		
Single pulse avalanche current	L = 0.1 mH	I <sub>AS</sub>	- 30		
Single pulse avalanche energy	L = 0.1 MH	E <sub>AS</sub>	45	mJ	
Maximum power dissipation <sup>b</sup>	T <sub>C</sub> = 25 °C	T <sub>C</sub> = 25 °C	7.14	w	
	T <sub>C</sub> = 125 °C	P <sub>D</sub>	2.4	vv	
Operating junction and storage temperature	e range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 175	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-ambient	PCB mount <sup>c</sup>	R <sub>thJA</sub>	85	°C/W	
Junction-to-foot (drain)		R <sub>thJF</sub>	21	0/10	

#### Notes

a. Package limited

b. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%$ 

c. When mounted on 1" square PCB (FR-4 material)

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PARAMETER	SYMBOL	TES	MIN.	TYP.	MAX.	UNIT	
Static		-					
Drain-source breakdown voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0, I <sub>D</sub> = - 250 μA		- 40	-	-	v
Gate-source threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	V <sub>GS</sub> , I <sub>D</sub> = - 250 μA	- 1.5	- 2.0	- 2.5	v
Gate-source leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	0 V, $V_{GS} = \pm 20$ V	-	-	± 100	nA
		$V_{GS} = 0 V$	V <sub>DS</sub> = - 40 V	-	-	- 1.0	
Zero gate voltage drain current	I <sub>DSS</sub>	$V_{GS} = 0 V$	$V_{DS} = -40 \text{ V}, \text{ T}_{J} = 125 ^{\circ}\text{C}$	-	-	- 50	μA
		$V_{GS} = 0 V$	$V_{DS} = -40 \text{ V}, \text{ T}_{J} = 175 ^{\circ}\text{C}$	-	-	- 150	
On-state drain current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = - 10 V	$V_{DS} \ge -5 V$	- 30	-	-	Α
		V <sub>GS</sub> = - 10 V	I <sub>D</sub> = - 10.5 A	-	0.011	0.014	Ω
Ducia composito en atata unaistanza a	<b>B</b>	V <sub>GS</sub> = - 10 V	I <sub>D</sub> = - 10.5 A, T <sub>J</sub> = 125 °C	-	-	0.020	
Drain-source on-state resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 10 V	I <sub>D</sub> = - 10.5 A, T <sub>J</sub> = 175 °C	-	-	0.024	
		V <sub>GS</sub> = - 4.5 V	l <sub>D</sub> = - 8.7 A	-	0.017	0.023	
Forward transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = -	- 15 V, I <sub>D</sub> = - 10.5 A	-	30	-	S
Dynamic <sup>b</sup>	•						
Input capacitance	C <sub>iss</sub>		0 V V <sub>DS</sub> = - 20 V, f = 1 MHz	-	3400	4250	pF
Output capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$		-	440	550	
Reverse transfer capacitance	C <sub>rss</sub>			-	350	436	
Total gate charge <sup>c</sup>	Qg			-	74	115	
Gate-source charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = - 10 V	$V_{DS} = -20 V$ , $I_{D} = -10.5 A$	-	11	-	nC
Gate-drain charge <sup>c</sup>	Q <sub>gd</sub>			-	16	-	
Gate resistance	R <sub>g</sub>		f = 1 MHz		-	3.21	Ω
Turn-on delay time <sup>c</sup>	t <sub>d(on)</sub>			-	58	85	
Rise time <sup>c</sup>	t <sub>r</sub>	$\label{eq:VDD} \begin{array}{l} V_{\text{DD}} = -15 \ V, \ R_{\text{L}} = 15 \ \Omega \\ I_{\text{D}} \cong -1 \ A, \ V_{\text{GEN}} = -4.5 \ V, \ R_{\text{g}} = 6 \ \Omega \end{array}$		-	76	105	
Turn-off delay time <sup>c</sup>	t <sub>d(off)</sub>			-	67	85	- ns
Fall time <sup>c</sup>	t <sub>f</sub>			-	44	55	
Source-Drain Diode Ratings and Char	acteristics <sup>b</sup>	•					
Pulsed current <sup>a</sup>	I <sub>SM</sub>			-	-	- 69	Α
Forward voltage	V <sub>SD</sub>	$I_{\rm F} = -2.7$ A, $V_{\rm GS} = 0$		-	- 0.8	- 1.1	V

Notes

a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %

b. Guaranteed by design, not subject to production testing

c. Independent of operating temperature

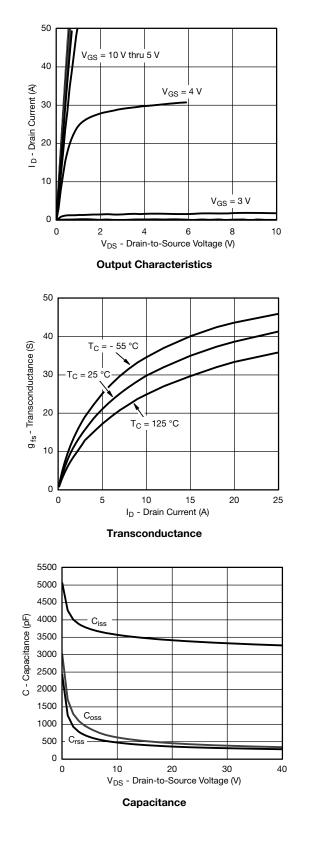
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

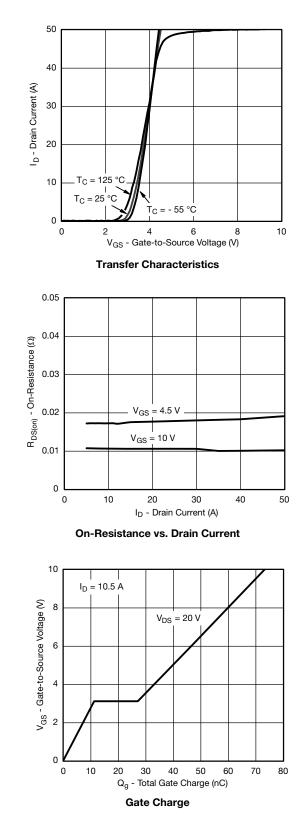
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## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)





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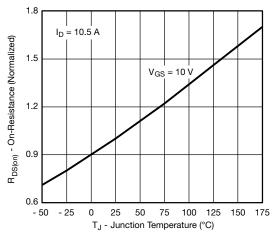
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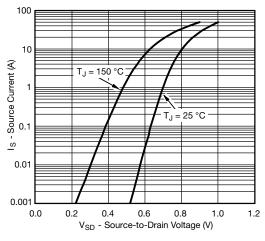
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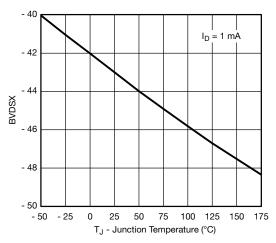
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



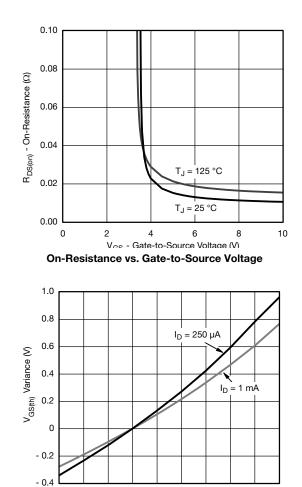
**On-Resistance vs. Junction Temperature** 



Source Drain Diode Forward Voltage



Breakdown Voltage vs. Junction Temperature

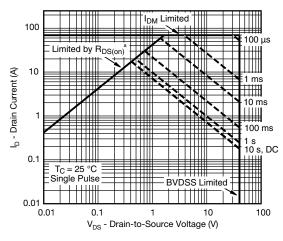


Threshold Voltage

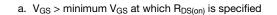
T<sub>J</sub> - Temperature (°C)

25 50 75 100 125

- 50 - 25 0



#### Safe Operating Area



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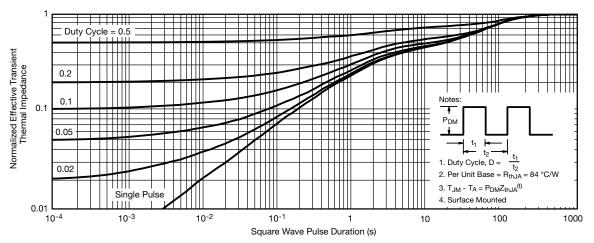
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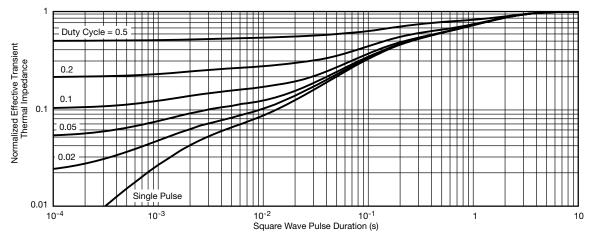


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### **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

#### Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Foot (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

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# Package Information

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# SOIC (NARROW): 8-LEAD JEDEC Part Number: MS-012





	MILLIMETERS		INC	HES	
DIM	Min	Мах	Min	Max	
A	1.35	1.75	0.053	0.069	
A <sub>1</sub>	0.10	0.20	0.004	0.008	
В	0.35	0.51	0.014	0.020	
С	0.19	0.25	0.0075	0.010	
D	4.80	5.00	0.189	0.196	
E	3.80	4.00	0.150	0.157	
е	e 1.27 BSC		0.050 BSC		
н	5.80	6.20	0.228	0.244	
h	0.25	0.50	0.010	0.020	
L	0.50	0.93	0.020	0.037	
q	0°	8°	0°	8°	
S	0.44	0.64	0.018	0.026	
ECN: C-06527-Rev. I, 11-Sep-06 DWG: 5498					

# **Application Note 826**

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**RECOMMENDED MINIMUM PADS FOR SO-8** 



Recommended Minimum Pads Dimensions in Inches/(mm)

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